	and the second second second			_ 11 1
L Number	Hits	Search Text	DB	Time stamp
Numer	1	("5976769").PN.	USPAT;	2003/08/14
-	_	( 3570705 ) . I.W.	US-PGPUB	14:16
	1154	(resist or photoresist or energy adj	USPAT:	2003/08/15
_	115,3	sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	14:36
	-	sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	11.30
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	i
		or trim\$4) and (liquid near3 etch\$3 or	TDM_TDB	'
				·
	610	isotropic\$4 near3 etch\$3))	ticpam.	2003/08/14
	610	((resist or photoresist or energy adj	USPAT;	
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	16:40
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM_TDB	l i
		or trim\$4) and (liquid near3 etch\$3 or		
	1	isotropic\$4 near3 etch\$3))) and		
	-	(semiconduct\$3 or optic\$4 or mask or		
		photomask or reticle).ti,ab.		
-	279	((resist or photoresist or energy adj	USPAT;	2003/08/14
ļ		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	18:25
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	
. ]	•	or trim\$4) and (liquid near3 etch\$3 or	_	
		isotropic\$4 near3 etch\$3))) and		. 1
		(430/5,296,313,316,317,321,329,330 or	•	1
		378/34,35 or		. "
		438/723,724,733-735,737,739,743,744,756,75	7	
		or 216/41,49).ccls.	-	
_	. 8	(((resist or photoresist or energy adj	USPAT;	2003/08/14
_	. 0	sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	18:35
			EPO; JPO;	10.33
		sensit\$4) same (develop\$4 and (reduc\$3 or shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	
			1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	
		or trim\$4) and (liquid near3 etch\$3 or		
		isotropic\$4 near3 etch\$3))) and		
•		(430/5, 296, 313, 316, 317, 321, 329, 330 or		
		378/34,35 or	<u> </u>	
		438/723,724,733-735,737,739,743,744,756,75	/	
		or 216/41,49).ccls.) and ("SiON" or	*	
		silicon adj oxynitride) same (\$1ARC or	,	
	•	antireflect\$3 or anti adj reflect\$3)		
_	151	(((resist or photoresist or energy adj	USPAT;	2003/08/15 .
,		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	14:13
*		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	40
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM_TDB	
		or trim\$4) and (liquid near3 etch\$3 or		
		isotropic\$4 near3 etch\$3))) and		
		(430/5,296,313,316,317,321,329,330 or		
		378/34,35 or		
		438/723,724,733-735,737,739,743,744,756,75	b ՝ :	
		or 216/41,49).ccls.) and (bak\$3 or	<u> </u>	
.		heat\$3) same (resist or photoresist or		
		energy adj sensit\$4 or photosensit\$4 or		
* . *		photo adj sensit\$4) not (((resist or	· · · · · · · · · · · · · · · · · ·	
		photoresist or energy adj sensit\$4 or		
				. ]
		photosensit\$4 or photo adj sensit\$4) same (develop\$4 and (reduc\$3 or shrink\$3 or		1
		decreas\$3 or less\$5 or slim\$4 or trim\$4)		[ ]
*		and (liquid near3 etch\$3 or isotropic\$4		, I
		near3 etch\$3))) and	ļ ·	·
		(430/5,296,313,316,317,321,329,330 or		.
		378/34,35 or	L ·	ļ į
	·	438/723,724,733-735,737,739,743,744,756,75	<b>/</b> /	
		or 216/41,49).ccls.) and ("SiON" or		.
	<u> </u>	silicon adj oxynitride) same (\$1ARC or	<u> </u>	
		antireflect\$3 or anti adi reflect\$3))		

(=	5	(((resist or photoresist or energy adj	USPAT;	2003/08/14
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	18:30
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
	,	shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	
		or trim\$4) and (liquid near3 etch\$3 or		
		isotropic\$4 near3 etch\$3))) and	*	
		(430/5,296,313,316,317,321,329,330 or		
		378/34,35 or	<b>.</b>	
	·.	438/723,724,733-735,737,739,743,744,756,75	ק	
}		or 216/41,49).ccls.) and (hardmask or		
		hard adj mask) same (\$1ARC or		
	3	antireflect\$3 or anti adj reflect\$3)		10. 5 2 4 5 5 1 1
-	1	"5472829".PN.	ŪSPAT;	2003/08/14
		X .	US-PGPUB	19:58
-	1	"5139904".PN.	USPAT;	2003/08/15
	_	Male - Carren Co.	US-PGPUB .	11:14
- · .	1	"5324676".PN.	USPAT;	2003/08/15
		#5.404.650# DV	US-PGPUB	11:26
<b>–</b> .	1	"5431770".PN.	USPAT;	2003/08/15
*		#5004000# PX	US-PGPUB	11:27   2003/08/15
-	1	"5804088".PN.	USPAT; US-PGPUB	11:30
	1	"5885887".PN.	USPAT:	2003/08/15
T .	1	"588588/".PN.	US-PGPÜB	11:58
	1	"5930634".PN.	USPAT;	2003/08/15
-	*	3930634 .PN.	US-PGPUB	12:01
L_	1	"5965461".PN.	USPAT;	2003/08/15
	*	3303401 .IN.	US-PGPUB	12:02
l _	1	"6020111".PN.	USPAT;	2003/08/15
*	_		US-PGPUB	12:14
_	1	"6121123".PN.	USPAT;	2003/08/15
- ) ( -	_	*	US-PGPUB	12:54
-	1	"6121123".PN.	USPAT;	2003/08/15
	[		US-PGPUB	13:03
-	1	"6156485".PN.	USPAT;	2003/08/15
	[		US-PGPUB	13:04
_	1 .1	"6194323".PN.	USPAT;	2003/08/15
			US-PGPUB	13:12
	1	"6277750".PN.	USPAT;	2003/08/15
			US-PGPUB	13:15
<b> </b>	1	"6281130".PN.	USPAT;	2003/08/15
			US-PGPUB	13:15
<b>–</b> • .	0		USPAT;	2003/08/15
		isotropic\$4 same (developer or solution	US-PGPUB;	14:16
		or solvent or etch\$3))	EPO; JPO;	
		1	IBM TDB	

			TIO D M	2002/00/15
-	138	(((resist or photoresist or energy adj	USPAT;	2003/08/15
1 1		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	14:34
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM_TDB	
. 1		or trim\$4) and (liquid near3 etch\$3 or		8
]		isotropic\$4 near3 etch\$3))) and		<i>'</i>
		(430/5,296,313,316,317,321,329,330 or		
		378/34,35 or   428/722 724 733-735 737 738 743 744 756 75	7	
		438/723,724,733-735,737,739,743,744,756,75 or 216/41,49).ccls.) and (expos\$3 or	<i>'</i>	
		pattern\$3 or radiat\$3 or irradiat\$3) same		
		(resist or photoresist or energy adj		. [
		sensit\$4 or photosensit\$4 or photo adj		, *
.		sensit\$4) same (x adj ray or extreme adj ultraviolet or EUV or extreme adj UV or		
		"157" adj nm or "193" adj nm or deep adj		
		ultraviolet or deep adj UV or DUV or i		
		adj line or particle adj beam or ion adj		
		beam or electron adj beam or e adj beam)	,	,
		not ((((resist or photoresist or energy		
		adj sensit\$4 or photosensit\$4 or photo		·
		adj sensit\$4 of photosensit\$4 of photo adj sensit\$4) same (develop\$4 and	*	
		(reduc\$3 or shrink\$3 or decreas\$3 or		
		less\$5 or slim\$4 or trim\$4) and (liquid		
		near3 etch\$3 or isotropic\$4 near3		
		etch\$3))) and		·
		(430/5,296,313,316,317,321,329,330 or		
		378/34,35 or	.	
		438/723,724,733-735,737,739,743,744,756,75	7	
		or 216/41,49).ccls.) and ("SiON" or	<b>,</b>	
		silicon adj oxynitride) same (\$1ARC or		•
<u> </u>	_	Anoxidaticol and oxymicitude, same (viake or anoxidation and oxymicitude)	USPAT;	2003/08/15
-		(developer or solution or solvent or	US-PGPUB;	14:16
ļ		etch\$3))	EPO; JPO;	
		CCC1143//	IBM TDB	· · · · · · · · · · · · · ·
_	622	(((resist or photoresist or energy adj	USPAT;	2003/08/15
1 <sup>-</sup>	022	sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	14:44
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	
		or trim\$4) and ((liquid or wet or solvent		
		or solution or isotropic\$4) near3		•
		etch\$3))) and		
		(430/5,296,313,316,317,321,329,330 or	00	*
		378/34,35 or		
		438/723,724,733-735,737,739,743,744,756,75	. ל	•
		or 216/41,49).ccls.) and (expos\$3 or		
.		pattern\$3 or radiat\$3 or irradiat\$3) same		
		(resist or photoresist or energy adj	•	
		sensit\$4 or photosensit\$4 or photo adj		·
		sensit\$4) same (x adj ray or extreme adj		
		ultraviolet or EUV or extreme adj UV or		
Y =	a a	"157" adj nm or "193" adj nm or deep adj		
		ultraviolet or deep adj UV or DUV or i	* * * * * * * * * * * * * * * * * * * *	
		adj line or particle adj beam or ion adj		
		beam or electron adj beam or e adj beam)	•	
		not ((((resist or photoresist or energy		·
		adj sensit\$4 or photosensit\$4 or photo		
.				•
		adl sensit\$4) same (develop\$4 and		
·		adj sensit\$4) same (develop\$4 and (reduc\$3 or shrink\$3 or decreas\$3 or		
		(reduc\$3 or shrink\$3 or decreas\$3 or		
		(reduc\$3 or shrink\$3 or decreas\$3 or less\$5 or slim\$4 or trim\$4) and (liquid		
		(reduc\$3 or shrink\$3 or decreas\$3 or less\$5 or slim\$4 or trim\$4) and (liquid near3 etch\$3 or isotropic\$4 near3		
		<pre>(reduc\$3 or shrink\$3 or decreas\$3 or less\$5 or slim\$4 or trim\$4) and (liquid near3 etch\$3 or isotropic\$4 near3 etch\$3))) and</pre>	-	
		(reduc\$3 or shrink\$3 or decreas\$3 or less\$5 or slim\$4 or trim\$4) and (liquid near3 etch\$3 or isotropic\$4 near3 etch\$3))) and (430/5,296,313,316,317,321,329,330 or	-	
		(reduc\$3 or shrink\$3 or decreas\$3 or less\$5 or slim\$4 or trim\$4) and (liquid near3 etch\$3 or isotropic\$4 near3 etch\$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or	7	
		(reduc\$3 or shrink\$3 or decreas\$3 or less\$5 or slim\$4 or trim\$4) and (liquid near3 etch\$3 or isotropic\$4 near3 etch\$3))) and (430/5,296,313,316,317,321,329,330 or	7	

_	1	((resist or photoresist or energy adj	USPAT;	2003/08/15
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	14:46
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	·
		or trim\$4) and (liquid or wet or solvent	_	
		or solution) and isotropic\$4 near3		
		etch\$3)) and liquid adj isotropic adj		
		etch\$3		
	617		USPAT:	2003/08/15
-	61/	sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	14:48
			EPO; JPO;	14.40
		sensit\$4) same (develop\$4 and (reduc\$3 or		
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM_TDB	
		or trim\$4) and (liquid or wet or solvent		
9		or solution) and isotropic\$4 near3		
		etch\$3)		0000 (00 (16
- !	2783	(resist or photoresist or energy adj	USPAT;	2003/08/16
7		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	10:53
		sensit\$4) same develop\$4 same	EPO; JPO;	
		(tetramethylammonium adj hydroxide or	IBM_TDB	1
l i		tetramethyl adj ammonium adj hydroxide or		
		TMAH)		*
_	41	((resist or photoresist or energy adj	USPAT;	2003/08/16
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	13:34
		sensit\$4) same develop\$4 same	EPO; JPO;	
		(tetramethylammonium adj hydroxide or	IBM TDB	
		tetramethyl adj ammonium adj hydroxide or	_	
		TMAH)) and (weak or mild) near3 develop\$4		
_	1	("2000112146").PN.	DERWENT	2003/08/16
	_			13:10
_	0	("10-285215").PN.	DERWENT	2003/08/16
ļ		, ,, ,,		13:10
_	1	("10285215").PN.	DERWENT	2003/08/16
	_	1 10200220 / 12111		13:10
<u>                                      </u>	29	(bak\$3 or heat\$3) same (resist or	USPAT;	2003/08/16
	29	photoresist) same (glass adj transition	US-PGPUB;	13:40
		adj temperature or "T.sub.g") same	EPO; JPO;	10.10
			IBM TDB	
		(novolac or novolak or \$6hydroxystyrene)	TOM IND	<u> </u>